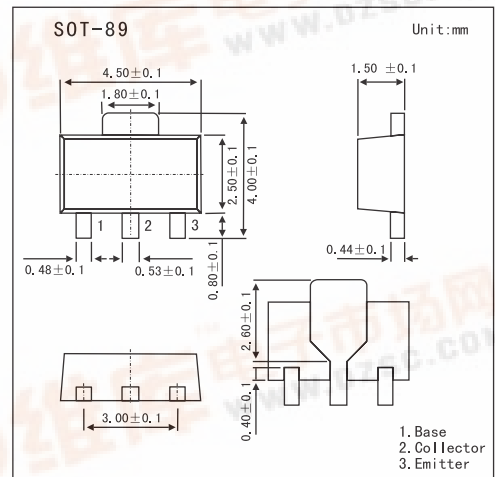


SMD Type Transistors

PNP Silicon Power Switching Transistor
FCX1149A

■ Features

- 2W power dissipation.
- 20A peak pulse current.
- Excellent HFE characteristics up to 10 Amps.
- Extremely low saturation voltage E.g. 45mv Typ.
- Extremely low equivalent on-resistance.
RCE(sat) 67mΩ at 3A.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-25	V
Emitter-base voltage	V _{EBO}	-5	V
Continuous collector current	I _{CM}	-10	A
Peak pulse current	I _C	-3	A
Base current	I _B	-500	mA
Power dissipation	P _{tot}	1	W
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

FCX1149A

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=-100μA	-30			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=-10mA	-25			V
Emitter-base breakdown voltage	V(BR)EBO	IE=-100μA	-5			V
Collector cut-off current	ICBO	VCE=-24V		-0.3	-100	nA
Collector Emitter Cut-Off Current	ICES	VCE=-20V		-0.3	-100	nA
Emitter Cut-Off Current	IEBO	VEB=-4V		-0.3	-100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=-0.1A, IB=-1mA IC=-0.5A, IB=-3mA IC=-1A, IB=-7mA IC=-3A, IB=-100mA IC=-4A, IB=-140mA		-45 -100 -140 -200 -230	-80 -170 -240 -300 -350	mV
Base-emitter saturation voltage *	VBE(sat)	IC=-3A, IB=-100mA		-930	-1050	mV
Base-emitter ON voltage *	VBE(on)	IC=-3A, VCE=-2V		-840	-1000	mV
Static Forward Current Transfer Ratio*	hFE	IC=-10mA, VCE=-2V IC=-0.5A, VCE=-2V IC=-3A, VCE=-2V IC=-5A, VCE=-2V IC=-10A, VCE=-2V	270 250 150 115	450 400 260 190 50	- 800	
Transitional frequency	fT	IC=-50mA, VCE=-10V, f=50MHz		135		MHz
Output capacitance	Cobo	VCE=-10V, f=1MHz		10		pF
Turn-on time	t(on)	IC=-4A, VCC=-10V		150		ns
Turn-off time	t(off)	IB1=IB2=-40mA		270		ns

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	149
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